

Write Amplification due to ECC on Flash Memory or Leave those Bit Errors Alone

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- Flash Memory Write Endurance
 - 10,000 P/E cycles for MLC
- Flash Memory Protection Scheme
 - Error Correcting Code (ECC)
 - Scrubbing
 - Wear-leveling and Garbage Collection
 - Parity protection (RAID)
- These protection schemes

 (+) Improve the reliability of flash memory
 (-) Amplify writes → Reduce the reliability of flash memory



Write amplification (W.A.)

- The number of excess writes / writes issued by system
- Main sources of W.A.
 - Copying live data in garbage collection
 - Writing corrected data back in ECC recovery
 - Parity update of RAID
- W.A. degrades
 - performance (related work)
 - flash memory's lifetime



- W.A. due to ECC recovery
 - Reads lead to writes







Traditional point of view to W.A.

Our point of view to W.A.

→ Severe problem with read intensive workload



- A statistical model
 - The impact of the W.A. to the lifetime of flash memory
- A loss of 48% of the lifetime due to the W.A.
 - Various parameters were tested
- Threshold-based ECC to reduce the W.A.
 - Improves the lifetime up to 64%
 - The way to control W.A. to maximize the lifetime



- Raw Bit Error Rate from measurement study
- Uncorrectable Page Error Rate (UPER)
 - A Canonical Markov Model





Uncorrectable Page Group Error Rate (UGER)



Mean Time to Data Loss

$$MTTDL_{p} = \lim_{k \to \infty} \sum_{j=1}^{k} \left(jg(j) \prod_{i=1}^{j-1} (1 - g(i)) \right)$$

The probability of uncorrectable page group error



Evaluation: Write Amplification

- More read, higher W.A.
- G.C. : -19% lifetime
- ECC : -42% lifetime
- G.C. + ECC : -48% lifetime

r:w	5000	10000	15000	20000	25000	30000
1:1	1.0302	1.0839	1.2125	1.4430	1.7011	1.8738
3:1	1.0308	1.0889	1.2475	1.6287	2.3165	3.0930
5:1	1.0309	1.0899	1.2560	1.6862	2.5968	3.9032
7:1	1.0310	1.0904	1.2598	1.7142	2.7571	4.4806
9:1	1.0310	1.0906	1.2619	1.7308	2.8609	4.9130

W.A. from ECC recovery at different P/E cycles



160GB 3x nm SSD 100MB/s Bandwidth 61bits correctable / 4KB 50% Device Utilization R:W=3:1

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1. Scrubbing may be harmful (not always)



3. Hotness helps to improve lifetime (efficient garbage collection)

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2. Lifetime highly depends on space utilization



4. RAID improves lifetime (Mirroring is the best since it splits read workload)

■ AFR=1% ■ AFR=5%



• A few bit errors accumulate before ECC correction

58.2% of recoveries for pages with <= 5 bit errors

n	5000	10000	15000	20000	25000
= 1	0.0286	0.0756	0.1657	0.2463	0.2105
≤ 3	0.0295	0.0823	0.2077	0.4022	0.4604
≤ 5	0.0295	0.0824	0.2096	0.4323	0.5824
> 5	6.57e-10	3.12e-7	8.50e-5	0.0072	0.1163

Probability distribution of the number of accumulated bit errors *n* when they are recovered by ECC



• A few bit errors accumulate before ECC correction

11.6% of recoveries for pages with > 5 bit errors

n	5000	10000	15000	20000	25000
= 1	0.0286	0.0756	0.1657	0.2463	0.2105
≤ 3	0.0295	0.0823	0.2077	0.4022	0.4604
≤ 5	0.0295	0.0824	0.2096	0.4323	0.5824
> 5	6.57e-10	3.12e-7	8.50e-5	0.0072	0.1163

Probability distribution of the number of accumulated bit errors *n* when they are recovered by ECC



IDEA: Postpone write until errors accumulate?





A Markov model for reliability analysis





- Evaluation
 - Optimal threshold depends on environment and # of devices
 - Lifetime improves up to 64%





Controlling W.A. to achieve max lifetime





- Reads lead to W.A.
 - A Statistical Reliability Model
 - A loss of 48% of the lifetime due to W.A.
- To control W.A. through two tools
 - Scrubbing for detecting latent errors
 - Threshold-based ECC for avoiding excessive recovery



Q & A

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